

# SGL160N60UF

## Ultra-Fast IGBT

### General Description

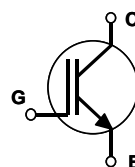
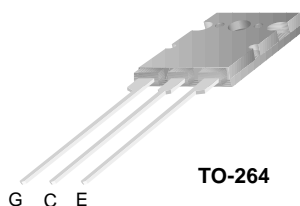
Fairchild's UF series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UF series is designed for applications such as motor control and general inverters where high speed switching is a required feature.

### Features

- High speed switching
- Low saturation voltage :  $V_{CE(sat)} = 2.1 \text{ V @ } I_C = 80 \text{ A}$
- High input impedance

### Applications

AC & DC motor controls, general purpose inverters, robotics, servo controls, and power supplies.



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	SGL160N60UF	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C = 25^\circ\text{C}$	160	A
	Collector Current @ $T_C = 100^\circ\text{C}$	80	A
$I_{CM(1)}$	Pulsed Collector Current	300	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	250	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	100	W
$T_J$	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	25	$^\circ\text{C/W}$

## Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\Delta B_{VCES}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	V/°C
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	uA
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 80mA, V_{CE} = V_{GE}$	3.5	4.5	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 80A, V_{GE} = 15V$	--	2.1	2.6	V
		$I_C = 160A, V_{GE} = 15V$	--	2.6	--	V
Dynamic Characteristics						
$C_{ies}$	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V, f = 1MHz$	--	5000	--	pF
$C_{oes}$	Output Capacitance		--	600	--	pF
$C_{res}$	Reverse Transfer Capacitance		--	200	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 80A, R_G = 3.9\Omega, V_{GE}=15V$ Inductive Load, $T_C = 25^\circ C$	--	40	--	ns
$t_r$	Rise Time		--	101	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	90	130	ns
$t_f$	Fall Time		--	75	150	ns
$E_{on}$	Turn-On Switching Loss		--	2500	--	uJ
$E_{off}$	Turn-Off Switching Loss	$V_{CC} = 300V, I_C = 80A, R_G = 3.9\Omega, V_{GE} = 15V$ Inductive Load, $T_C = 125^\circ C$	--	1760	--	uJ
$E_{ts}$	Total Switching Loss		--	4260	5000	uJ
$t_{d(on)}$	Turn-On Delay Time		--	45	--	ns
$t_r$	Rise Time		--	105	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	140	200	ns
$t_f$	Fall Time	$V_{CE} = 300V, I_C = 80A, V_{GE} = 15V$	--	122	250	ns
$E_{on}$	Turn-On Switching Loss		--	2785	--	uJ
$E_{off}$	Turn-Off Switching Loss		--	3100	--	uJ
$E_{ts}$	Total Switching Loss		--	5885	--	uJ
$Q_g$	Total Gate Charge		--	345	520	nC
$Q_{ge}$	Gate-Emitter Charge	Measured 5mm from PKG	--	60	100	nC
$Q_{gc}$	Gate-Collector Charge		--	95	150	nC
$L_e$	Internal Emitter Inductance		--	18	--	nH

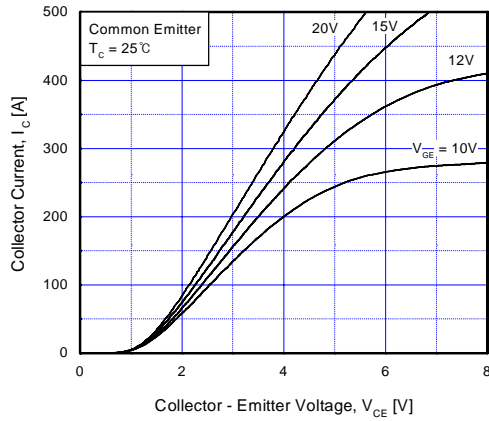


Fig 1. Typical Output Characteristics

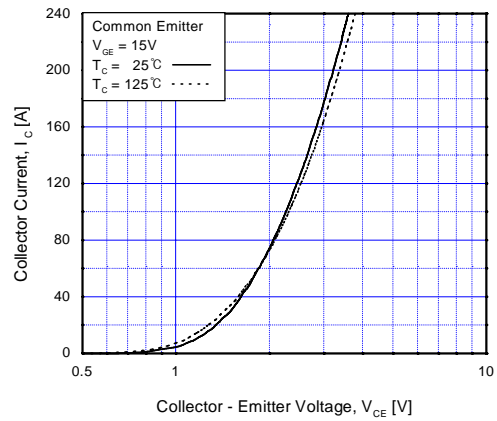


Fig 2. Typical Saturation Voltage Characteristics

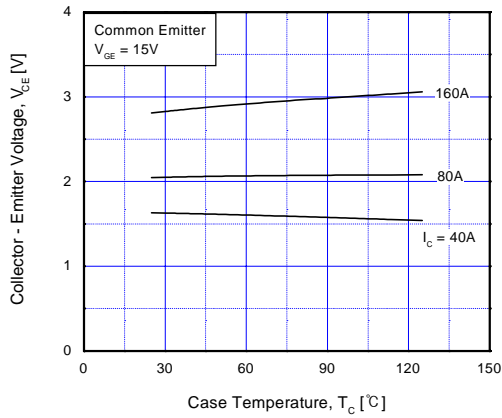


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

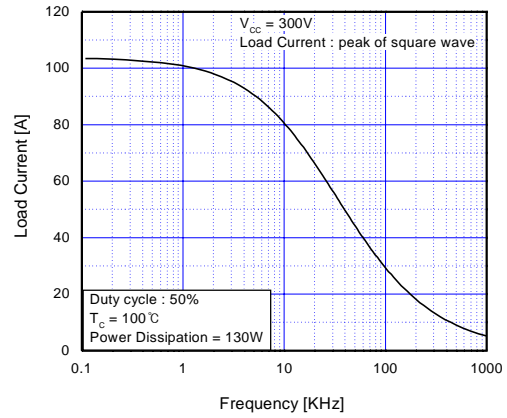


Fig 4. Load Current vs. Frequency

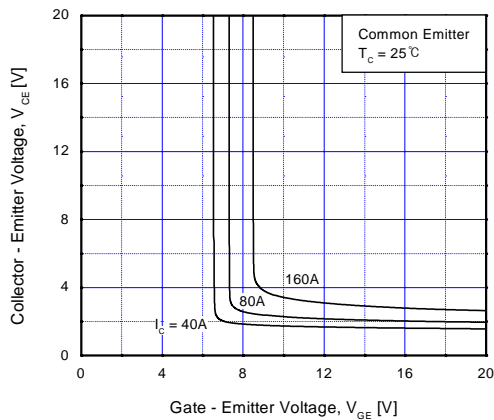


Fig 6. Saturation Voltage vs.  $V_{GE}$

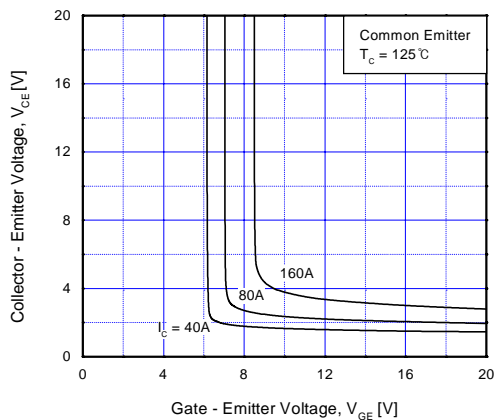


Fig 7. Saturation Voltage vs.  $V_{GE}$

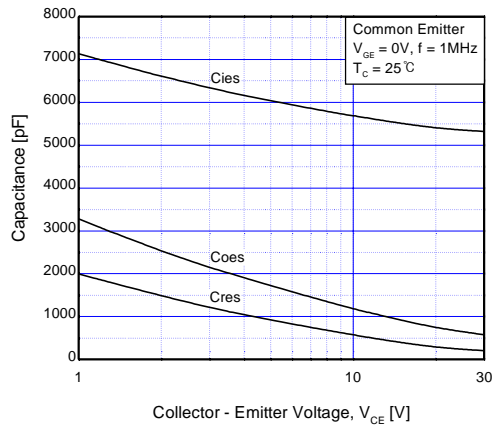


Fig 7. Capacitance Characteristics

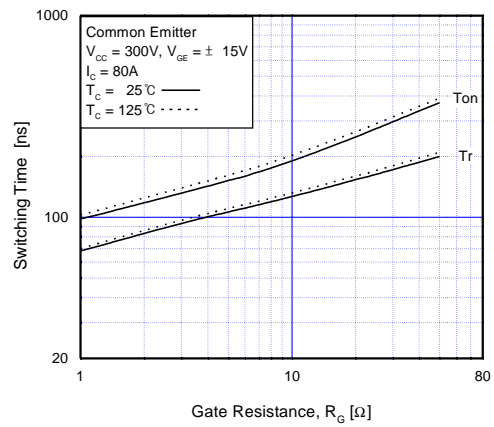


Fig 8. Turn-On Characteristics vs. Gate Resistance

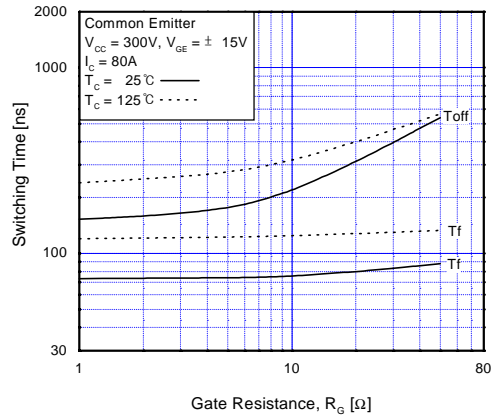


Fig 9. Turn-Off Characteristics vs. Gate Resistance

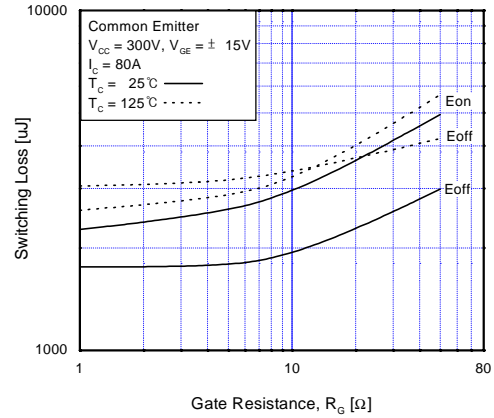


Fig 10. Switching Loss vs. Gate Resistance

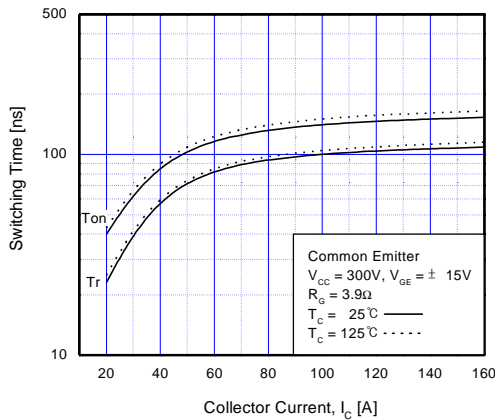


Fig 11. Turn-On Characteristics vs. Collector Current

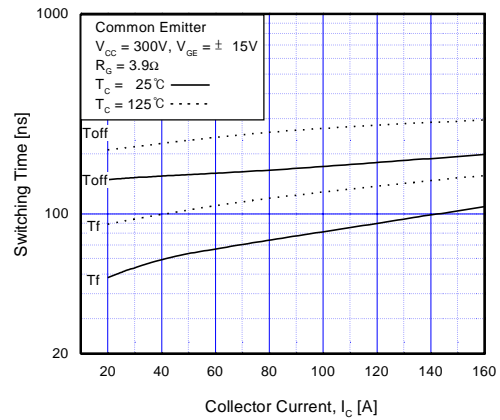


Fig 12. Turn-Off Characteristics vs. Collector Current

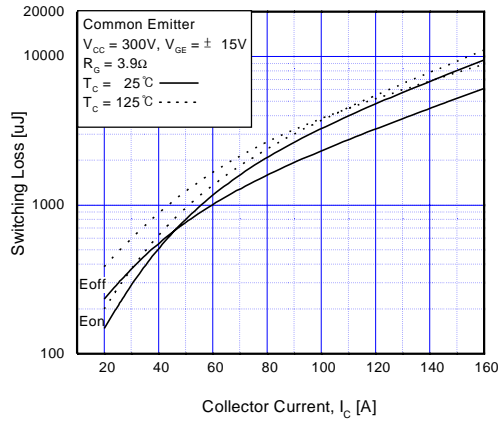


Fig 13. Switching Loss vs. Collector Current

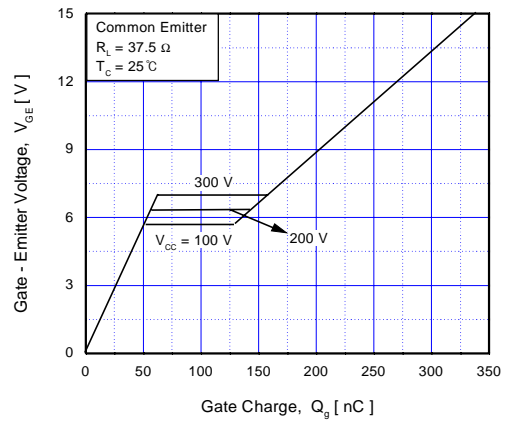


Fig 14. Gate Charge Characteristics

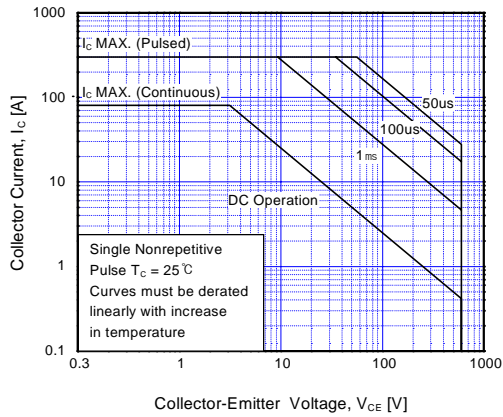


Fig 15. SOA Characteristic

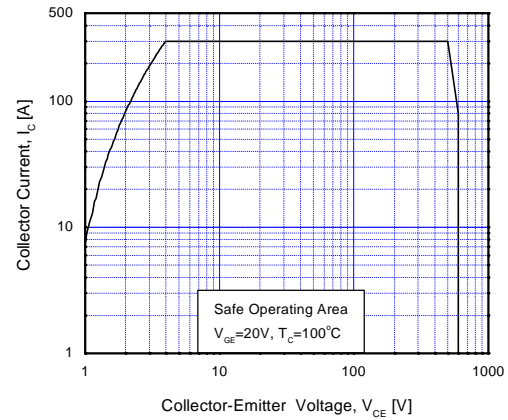


Fig 16. Turn-Off SOA Characteristics

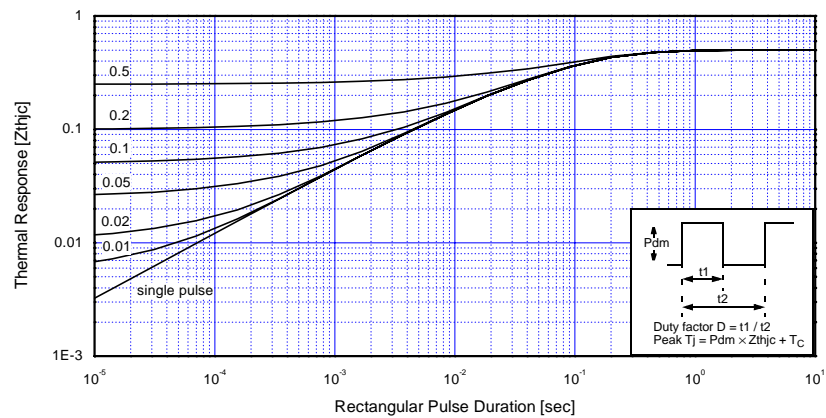


Fig 17. Transient Thermal Impedance of IGBT

**SGL160N60UF**

Technical drawing of a mechanical part, likely a bracket or base plate, showing top and side views with dimensions in millimeters.

**Top View Dimensions:**

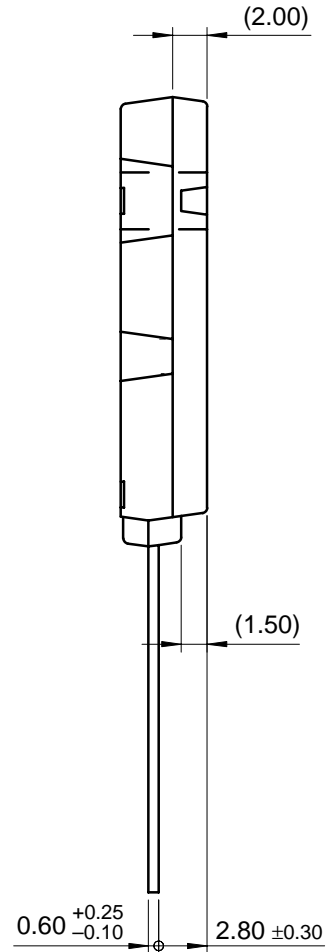
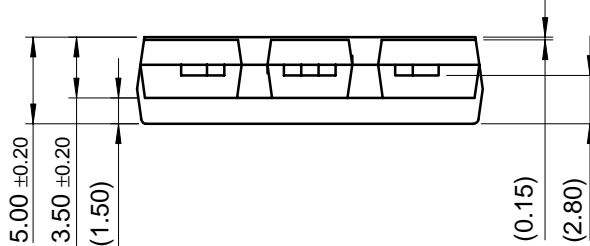
- Overall width:  $20.00 \pm 0.20$
- Overall height:  $20.00 \pm 0.20$
- Distance from top edge to center line:  $10.00$  (split into  $8.30$  and  $8.30$ )
- Distance from left edge to center line:  $10.00$  (split into  $8.30$  and  $1.70$ )
- Distance from right edge to center line:  $10.00$  (split into  $8.30$  and  $1.70$ )
- Distance from bottom edge to center line:  $10.00$  (split into  $8.30$  and  $1.70$ )
- Central hole diameter:  $\varnothing 3.30 \pm 0.20$
- Corner hole radius:  $R1.00$  and  $R2.00$
- Distance from center line to corner hole center:  $7.00$
- Distance from center line to corner hole center:  $7.00$
- Distance from center line to corner hole center:  $7.00$
- Distance from center line to corner hole center:  $7.00$

**Side View Dimensions:**

- Overall height:  $20.00 \pm 0.20$
- Distance from top edge to center line:  $10.00$  (split into  $8.30$  and  $1.70$ )
- Distance from left edge to center line:  $10.00$  (split into  $8.30$  and  $1.70$ )
- Distance from right edge to center line:  $10.00$  (split into  $8.30$  and  $1.70$ )
- Distance from bottom edge to center line:  $10.00$  (split into  $8.30$  and  $1.70$ )
- Central hole diameter:  $\varnothing 3.30 \pm 0.20$
- Corner hole radius:  $R1.00$  and  $R2.00$
- Distance from center line to corner hole center:  $7.00$
- Distance from center line to corner hole center:  $7.00$
- Distance from center line to corner hole center:  $7.00$
- Distance from center line to corner hole center:  $7.00$

**Material and Tolerances:**

- Material: 5.45TYP
- Tolerance:  $[5.45 \pm 0.30]$



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